

## **ABSTRACT OF THE DISCLOSURE**

[0052] The present invention discloses an ALD method including: respectively loading a plurality of substrates into a plurality of reaction cells, the plurality of reaction cells being disposed in a reaction chamber isolated from an exterior condition; alternately and repeatedly applying various vapor substances onto each substrate such that a thin film is formed on each substrate, wherein a plurality of vapor injection pipes each injecting one of the vapor substances periodically scans over each substrate to apply the various vapor substances alternately and repeatedly onto each substrate.

[0053] In another aspect, the present invention discloses a semiconductor device fabricating apparatus including: a plurality of susceptors on which the same number of substrates are respectively mounted; a reaction chamber isolating all the substrates on the plurality of susceptors from an exterior condition; a plurality of vapor injection pipes disposed over the substrates, each vapor injection pipe relatively rotating with respect to the substrates and periodically applying a vapor substance onto each substrate; a plurality of exhausting portion each disposed near a corresponding susceptor to exhaust a remaining vapor substance out of the reaction chamber.